

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C (t<10s)
-30V	7.0mΩ @ V <sub>GS</sub> = -10V	-17A
	10.0mΩ @ V <sub>GS</sub> = -4.5V	-13A

## Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

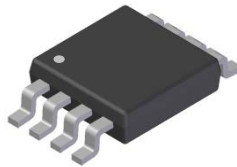
## Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

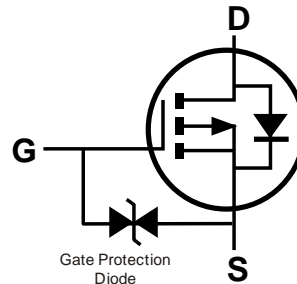
- Backlighting
- Power Management Functions
- DC-DC Converters

## Mechanical Data

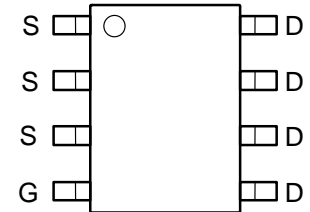
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram Below
- Terminals: Finish—Matte Tin Annealed Over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **e3**
- Weight: 0.074 grams (Approximate)



Top View



Internal Schematic



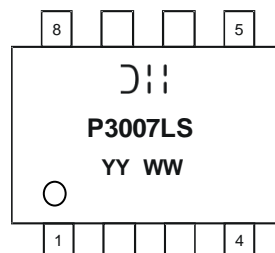
Top View  
Pin Configuration

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3007LSS-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



⌋⌋ = Manufacturer's Marking  
 P3007LS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Year (ex: 18 = 2018)  
 WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	-30	V	
Gate-Source Voltage		V <sub>GSS</sub>	±25	V	
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	Steady State	I <sub>D</sub>	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	-14 -11.5	A
	t < 10s		T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	-17 -12.5	A
Maximum Continuous Body Diode Forward Current (Note 6)		I <sub>S</sub>	-16.5	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	-120	A	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	-120	A	
Avalanche Current, L=1mH (Note 7)		I <sub>AS</sub>	-13	A	
Avalanche Energy, L=1mH (Note 7)		E <sub>AS</sub>	87	mJ	

**Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	91	°C/W
	t < 10s		51	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	59	°C/W
	t < 10s		48	°C/W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	9	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	—	-2.8	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	4.1	7	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -17A
		—	5.9	10		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -15A
		—	6.4	12		V <sub>GS</sub> = -4.0V, I <sub>D</sub> = -13A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS</b> (Note 9)						
Input Capacitance	C <sub>iss</sub>	—	2826	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	606	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	305	—	pF	
Gate Resistance	R <sub>g</sub>	—	22.8	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	31.2	—	nC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -11.5A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	64.2	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	10.6	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	11.6	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.8	—	ns	
Turn-On Rise Time	t <sub>R</sub>	—	4.3	—	ns	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V, R <sub>g</sub> = 6Ω, I <sub>D</sub> = -11.5A
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	306	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	125	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	19	—	ns	I <sub>S</sub> = -11.5A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	9.8	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

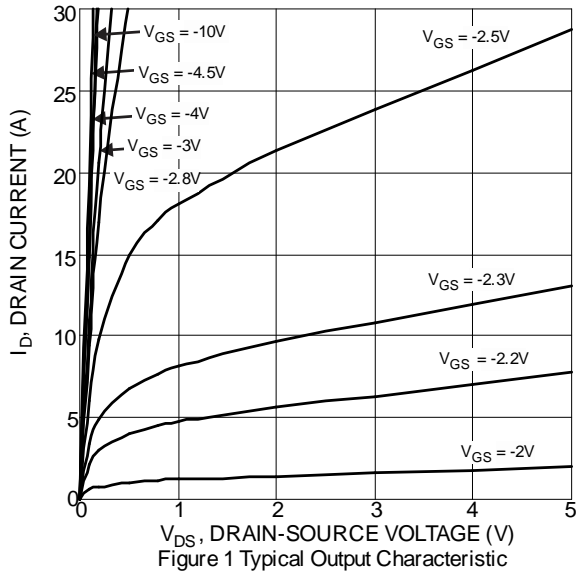


Figure 1 Typical Output Characteristic

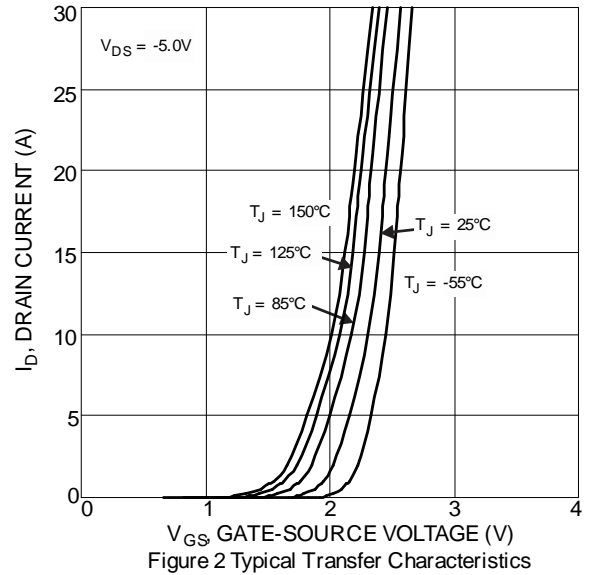


Figure 2 Typical Transfer Characteristics

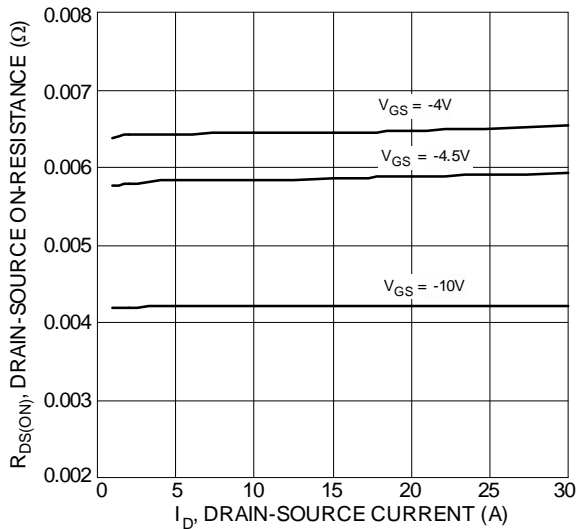


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

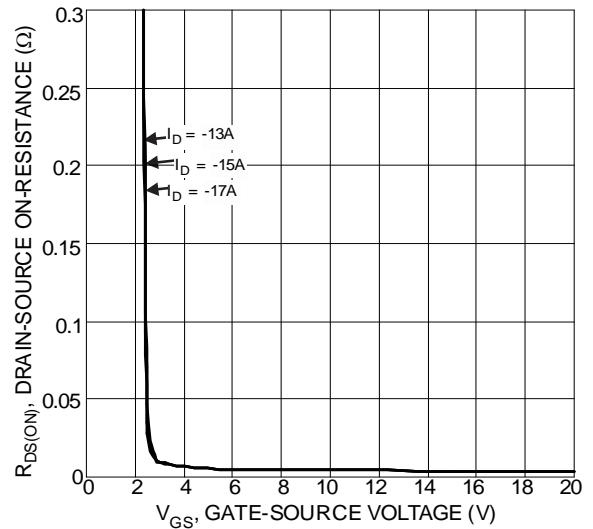


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

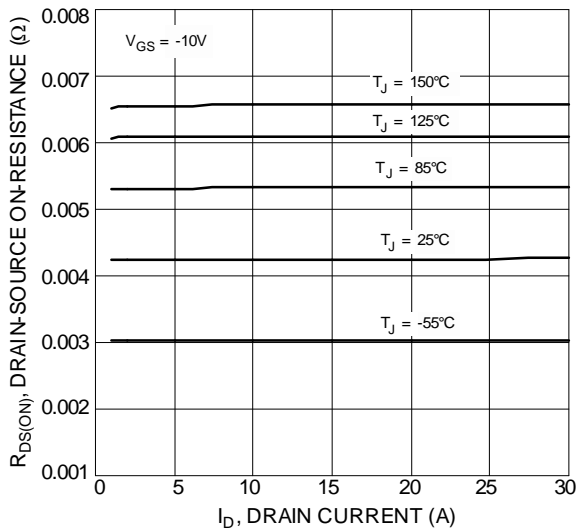


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

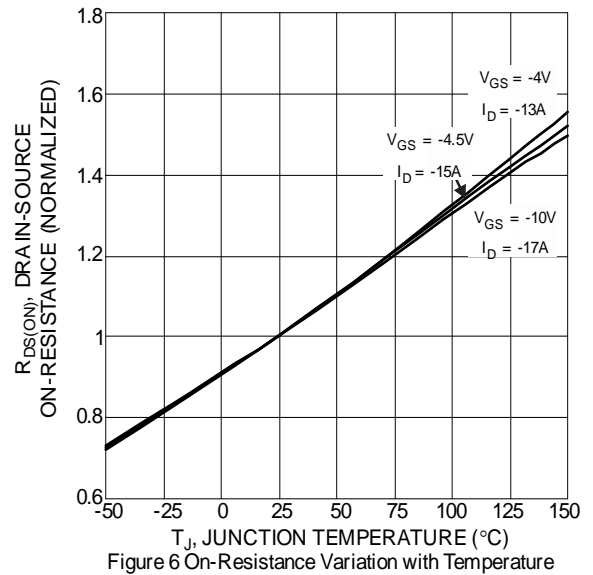


Figure 6 On-Resistance Variation with Temperature

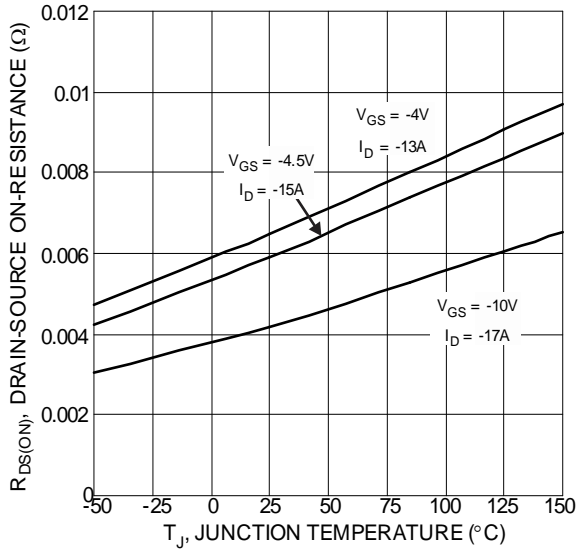


Figure 7 On-Resistance Variation with Temperature

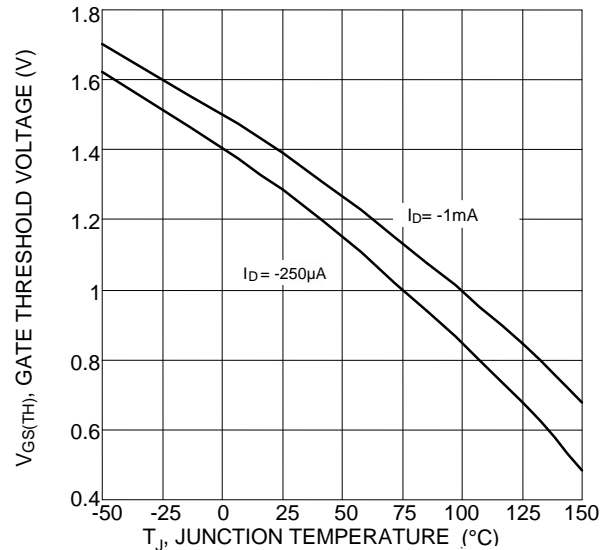


Figure 8 Gate Threshold Variation vs. Junction Temperature

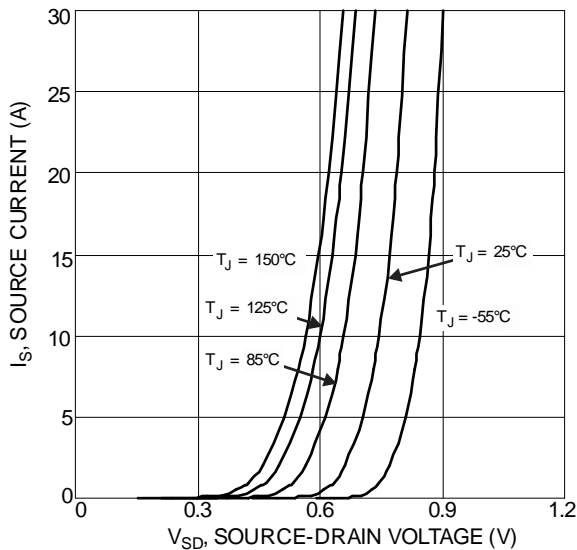


Figure 9 Diode Forward Voltage vs. Current

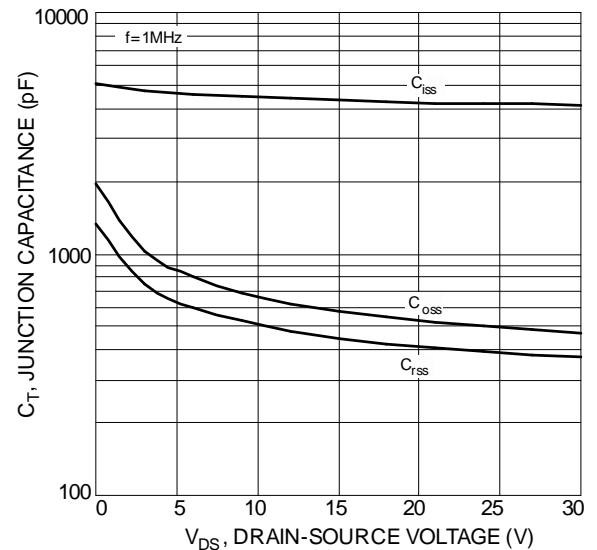


Figure 10 Typical Junction Capacitance

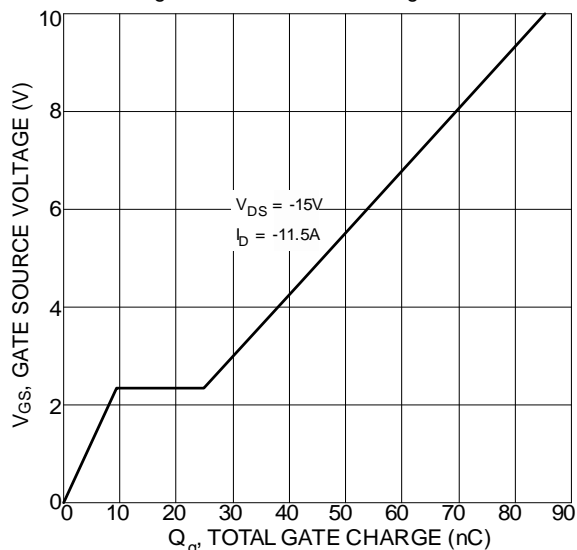


Figure 11 Gate Charge

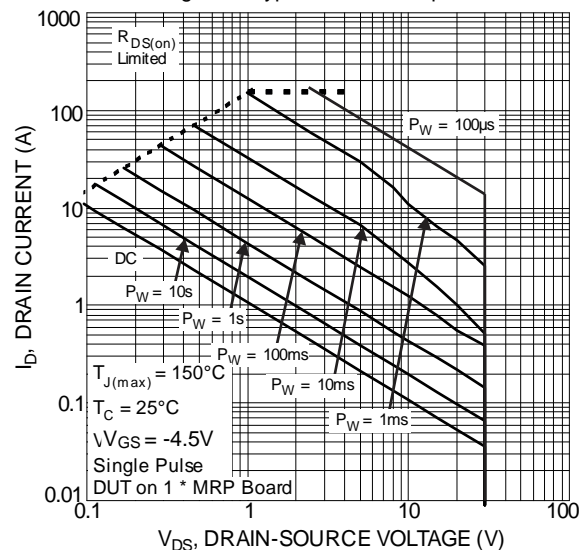
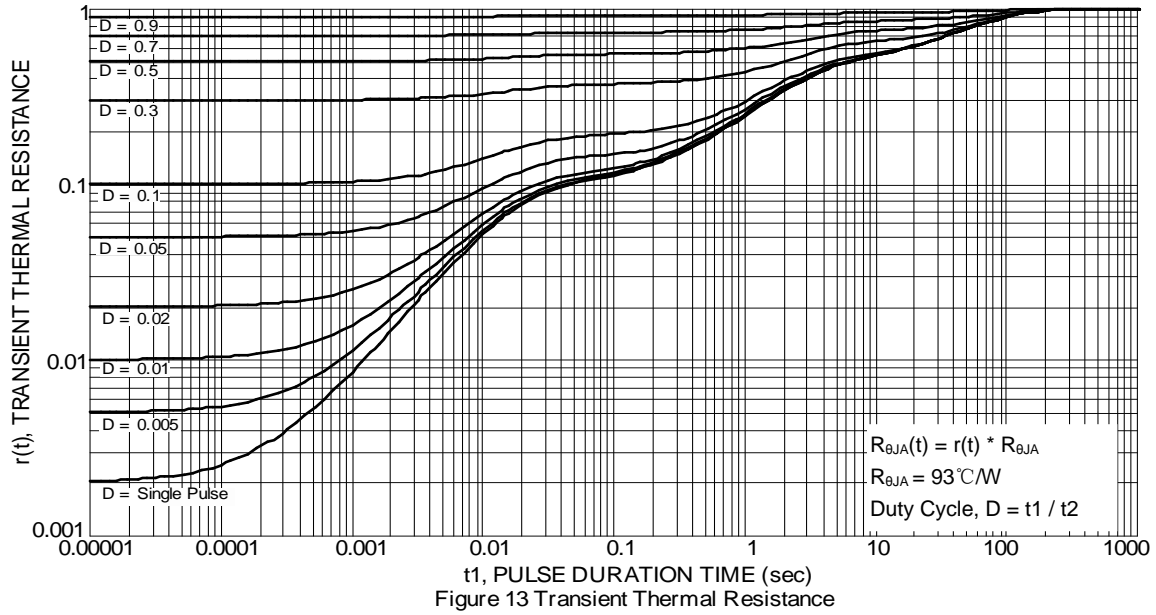


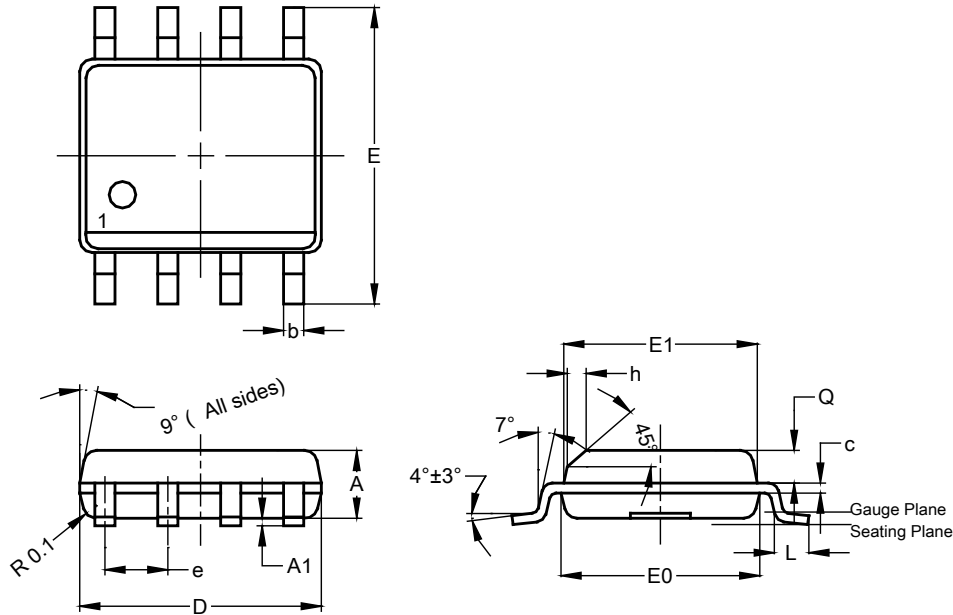
Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**

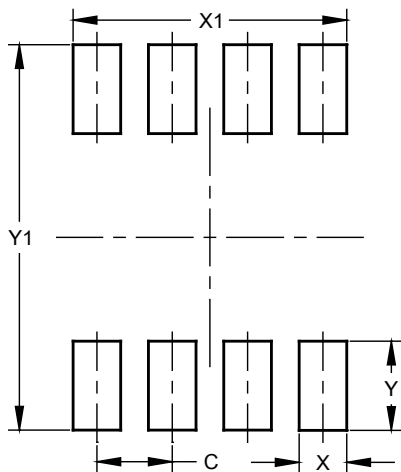


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	—	—	1.27
h	—	—	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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